Product data sheet

#### **Product profile** 1.

## 1.1 General description

Dual ultrafast power diode in a SOT226A (I2PAK) low-profile plastic package.

### 1.2 Features and benefits

- High reverse voltage surge capability
- High thermal cycling performance
- Low thermal resistance

- Soft recovery characteristic minimizes power consuming oscillations
- Very low on-state loss

## 1.3 Applications

Output rectifiers in high-frequency switched-mode power supplies

### 1.4 Quick reference data

Table 1. **Quick reference data** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	-	200	V
I <sub>O(AV)</sub>	average output current	square-wave pulse; $\delta$ = 0.5; $T_{mb} \le 104 \text{ C}$ ; both diodes conducting; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	30	Α
I <sub>FSM</sub>	non-repetitive peak forward current	$T_{j(init)}$ = 25 °C; t <sub>p</sub> = 10 ms; sine-wave pulse; per diode	-	-	160	Α
I <sub>RRM</sub>	repetitive peak reverse current	$t_p = 2 \ \mu s; \ \delta = 0.001$	-	-	0.2	Α
V <sub>ESD</sub>	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 k $\Omega$ ; all pins	-	-	8	kV
Static cha	racteristics					
V <sub>F</sub>	forward voltage	$I_F = 15 \text{ A}; T_j = 150 ^{\circ}\text{C};$ see Figure 4	-	0.78	0.85	V



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic ch	naracteristics					
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 100 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ C}$ ; ramp recovery; see Figure 5	-	20	28	ns
		$I_R = 1 \text{ A}; I_F = 0.5 \text{ A}; T_j = 25 \text{ C};$ step recovery; measured at reverse current = 0.25 A; see Figure 6	-	13	22	ns

# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		
2	K	cathode		A1 + + A2
3	A2	anode 2	0	<u> </u>
mb	К	mounting base; connected to cathode	1 2 3	sym125
			SOT226A (I2PAK)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYV42G-200	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226A

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		,			
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	200	V
$V_{RWM}$	crest working reverse voltage		-	200	V
$V_R$	reverse voltage	DC	-	200	V
I <sub>O(AV)</sub>	average output current	square-wave pulse; $\delta = 0.5$ ; $T_{mb} \le 104$ °C; both diodes conducting; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	30	A
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; t <sub>p</sub> = 25 µs; T <sub>mb</sub> ≤ 104 °C; per diode	-	30	Α
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	-	150	Α
		$t_p$ = 10 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; per diode	-	160	Α
I <sub>RRM</sub>	repetitive peak reverse current	$\delta = 0.001 \; ; \; t_p = 2 \; \mu s$	-	0.2	Α
I <sub>RSM</sub>	non-repetitive peak reverse current	t <sub>p</sub> = 100 μs	-	0.2	Α
T <sub>stg</sub>	storage temperature		-40	150	${\mathcal C}$
T <sub>j</sub>	junction temperature		-	150	${\mathbb C}$
V <sub>ESD</sub>	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 k $\Omega$ ; all pins	-	8	kV

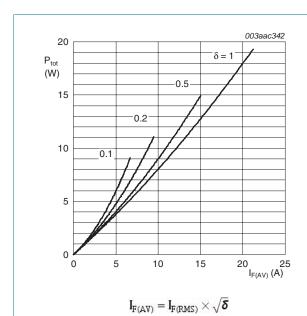
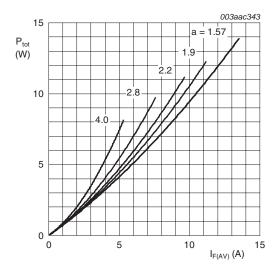


Fig 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



 $a = form \ factor = I_{F(RMS)} \, / \, I_{F(AV)}$ 

Fig 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j\text{-}mb)}$	thermal resistance from junction to mounting base	with heatsink compound; both diodes conducting	-	-	1.4	K/W
		with heatsink compound; per diode; see Figure 3	-	-	2.4	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

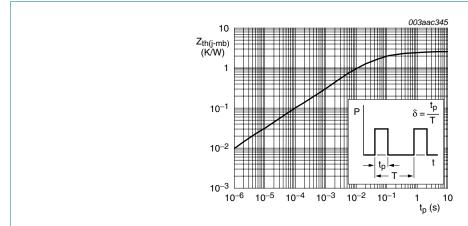
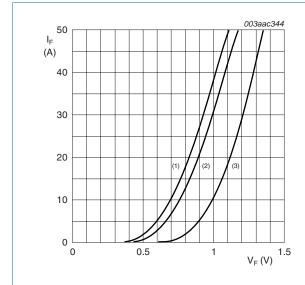


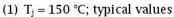
Fig 3. Transient thermal impedance from junction to mounting base as a function of pulse width

## 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>F</sub>	forward voltage	$I_F = 15 \text{ A}$ ; $T_j = 150  \text{C}$ ; see Figure 4	-	0.78	0.85	V
		$I_F = 15 \text{ A}; T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 4}}{}$	-	0.95	1.05	V
		$I_F = 30 \text{ A}; T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 4}}{}$	-	1	1.2	V
I <sub>R</sub> reverse current	reverse current	$V_R = 200 \text{ V}; T_j = 100 ^{\circ}\text{C}$	-	0.5	1	mA
	$V_R = 200 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	10	100	μΑ	
Dynamic ch	naracteristics					
Q <sub>r</sub>	recovered charge	$I_F$ = 2 A; $V_R$ = 30 V; $dI_F/dt$ = 20 A/ $\mu$ s; $T_j$ = 25 °C	-	6	15	nC
t <sub>rr</sub> reverse r	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 100 \text{ A/}\mu\text{s}$ ; ramp recovery; $T_j = 25 \text{ C}$ ; see Figure 5	-	20	28	ns
		$I_F = 0.5 \text{ A}$ ; $I_R = 1 \text{ A}$ ; step recovery; measured at reverse current = 0.25 A; $T_j = 25 \text{ C}$ ; see Figure 6	-	13	22	ns
$V_{FR}$	forward recovery voltage	$I_F = 1 \text{ A}$ ; $dI_F/dt = 10 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ C}$ ; see Figure 7	-	-	1	V





- (2)  $T_j = 150$  °C; maximum values
- (3)  $T_j = 25$ °C; maximum values

Fig 4. Forward current as a function of forward voltage

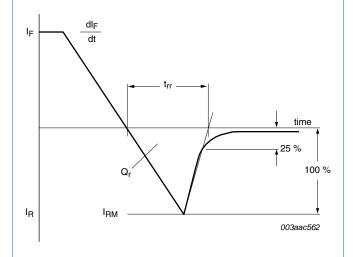
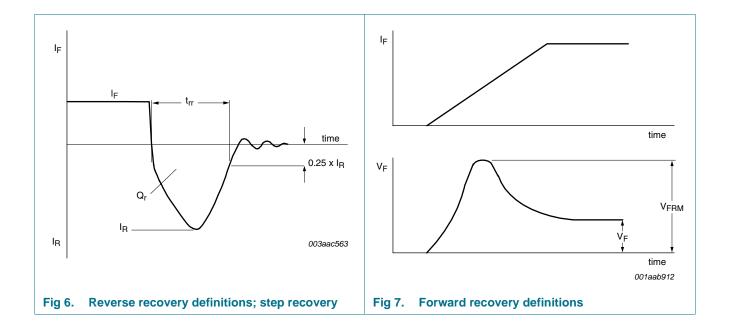


Fig 5. Reverse recovery definitions; ramp recovery



# 7. Package outline

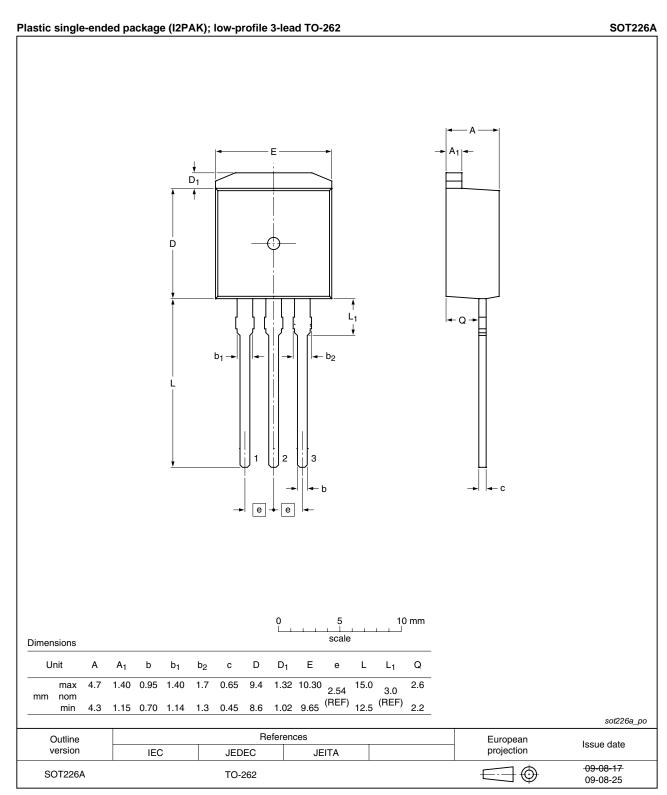


Fig 8. Package outline SOT226A (I2PAK)

BYV42G-200

**Dual ultrafast power diode** 

# 8. Revision history

### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYV42G-200 v.1	20110111	Product data sheet	-	-

## 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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